

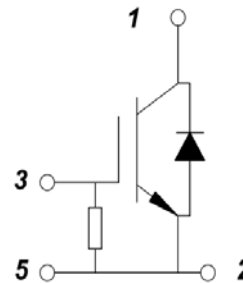
PRODUCT FEATURES

- IGBT³ CHIP(Trench+Field Stop technology)
- High short circuit capability,self limiting short circuit current
- $V_{CE(sat)}$ with positive temperature coefficient
- Fast switching and short tail current
- Free wheeling diodes with fast and soft reverse recovery
- Low switching losses
- 10K Ω Gate Protected Resistance Inside



APPLICATIONS

- High Power Converters
- Medical applications
- Motion/servo control
- UPS systems/Wind Turbines



IGBT-Inverter

ABSOLUTE MAXIMUM RATINGS

$T_C=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter/Test Conditions		Values	t
V_{CES}	Collector Emitter Voltage	$T_J=25^\circ\text{C}$	600	V
V_{GES}	Gate Emitter Voltage		± 20	
I_C	DC Collector Current	$T_C=25^\circ\text{C}$	950	A
		$T_C=60^\circ\text{C}$	800	
I_{CM}	Repetitive Peak Collector Current	$t_p=1\text{ms}$	1600	
P_{tot}	Power Dissipation Per IGBT		2100	W

Reverse-Diode

ABSOLUTE MAXIMUM RATINGS

$T_C=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter/Test Conditions		Values	t
V_{RRM}	Repetitive Reverse Voltage	$T_J=25^\circ\text{C}$	600	V
$I_{F(AV)}$	Average Forward Current	$T_C=25^\circ\text{C}$	800	A
I_{FRM}	Repetitive Peak Forward Current	$t_p=1\text{ms}$	1600	
I^2t		$T_J=125^\circ\text{C}, t=10\text{ms}, V_R=0\text{V}$	51200	A^2S

IGBT-Inverter
ELECTRICAL CHARACTERISTICS
 $T_C=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	t	
$V_{GE(th)}$	Gate Emitter Threshold Voltage	$V_{CE}=V_{GE}, I_C=12.8\text{mA}$	4.9	5.8	6.5		
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$I_C=800\text{A}, V_{GE}=15\text{V}, T_J=25^{\circ}\text{C}$		1.45	1.9	V	
		$I_C=800\text{A}, V_{GE}=15\text{V}, T_J=125^{\circ}\text{C}$		1.6			
I_{CES}	Collector Leakage Current	$V_{CE}=600\text{V}, V_{GE}=0\text{V}, T_J=25^{\circ}\text{C}$			1	mA	
		$V_{CE}=600\text{V}, V_{GE}=0\text{V}, T_J=125^{\circ}\text{C}$			10	mA	
I_{GES}	Gate Leakage Current	$V_{CE}=0\text{V}, V_{GE}=\pm 15\text{V}, T_J=125^{\circ}\text{C}$	-400		400	nA	
R_{gint}	Integrated Gate Resistor			0.5		Ω	
Q_g	Gate Charge	$V_{CE}=300\text{V}, I_C=800\text{A}, V_{GE}=\pm$		8.6		μC	
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, V_{GE}=0\text{V}, f=1\text{MHz}$		52		nF	
C_{res}	Reverse Transfer Capacitance				1.6		nF
$t_{d(on)}$	Turn on Delay Time	$V_{CC}=300\text{V}, I_C=800\text{A}$ $R_G=1.0\Omega,$ $V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^{\circ}\text{C}$		260		ns
			$T_J=125^{\circ}\text{C}$		290		ns
t_r	Rise Time	Inductive Load	$T_J=25^{\circ}\text{C}$		70		ns
			$T_J=125^{\circ}\text{C}$		90		ns
$t_{d(off)}$	Turn off Delay Time	$V_{CC}=300\text{V}, I_C=800\text{A}$ $R_G=1.0\Omega,$ $V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^{\circ}\text{C}$		450		ns
			$T_J=125^{\circ}\text{C}$		520		ns
t_f	Fall Time	Inductive Load	$T_J=25^{\circ}\text{C}$		90		ns
			$T_J=125^{\circ}\text{C}$		100		ns
E_{on}	Turn on Energy	$V_{CC}=300\text{V}, I_C=800\text{A}$ $R_G=1.0\Omega,$ $V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^{\circ}\text{C}$		11		mJ
			$T_J=125^{\circ}\text{C}$		17		mJ
E_{off}	Turn off Energy	Inductive Load	$T_J=25^{\circ}\text{C}$		25		mJ
			$T_J=125^{\circ}\text{C}$		29		mJ
I_{sc}	Short Circuit Current	$t_{psc}\leq 6\mu\text{S}, V_{GE}=15\text{V}$ $T_J=125^{\circ}\text{C}, V_{CC}=360\text{V}$		3500		A	
R_{thJC}	Junction to Case Thermal Resistance (Per IGBT)				0.07	K/W	

Reverse-Diode
ELECTRICAL CHARACTERISTICS
 $T_C=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	t
V_F	Forward Voltage	$I_F=800\text{A}, V_{GE}=0\text{V}, T_J=25^{\circ}\text{C}$		1.55	1.9	V
		$I_F=800\text{A}, V_{GE}=0\text{V}, T_J=125^{\circ}\text{C}$		1.5		
I_{RRM}	Max. Reverse Recovery Current	$I_F=800\text{A}, V_R=300\text{V}$		950		A
Q_{RR}	Reverse Recovery Charge	$di_F/dt=-9000\text{A}/\mu\text{s}$		65		μC
E_{rec}	Reverse Recovery Energy	$T_J=125^{\circ}\text{C}$		17.6		mJ
R_{thJCD}	Junction to Case Thermal Resistance (Per Diode)				0.12	K/W

MODULE CHARACTERISTICS

$T_C=25^{\circ}\text{C}$ unless otherwise sp

Symbol	Parameter/Test Conditions		Values	t
T_{Jmax}	Max. Junction Temperature		175	°C
T_{Jop}	Operating Temperature		-40~150	
T_{stg}	Storage Temperature		-40~125	
V_{isol}	Isolation Breakdown Voltage	AC, 50Hz(R.M.S), t=1minute	3000	V
Torque	to heatsink	Recommended (M6)	3~5	Nm
	to terminal	Recommended (M6)	2.5~5	Nm
	to terminal	Recommended (M4)	0.7~1.1	Nm
Weight			330	g

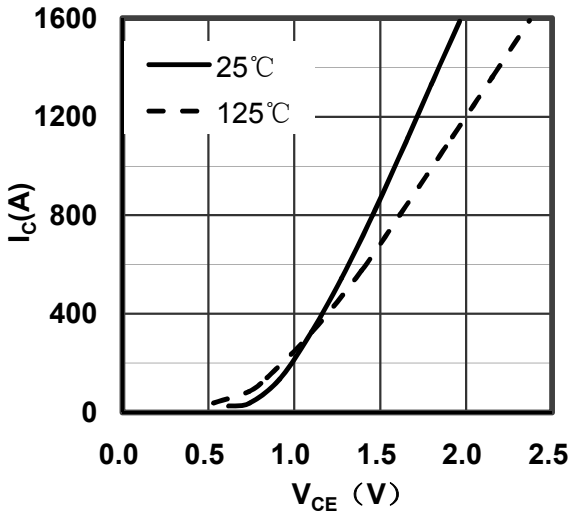


Figure 1. Typical Output Characteristics IGBT-Inverter

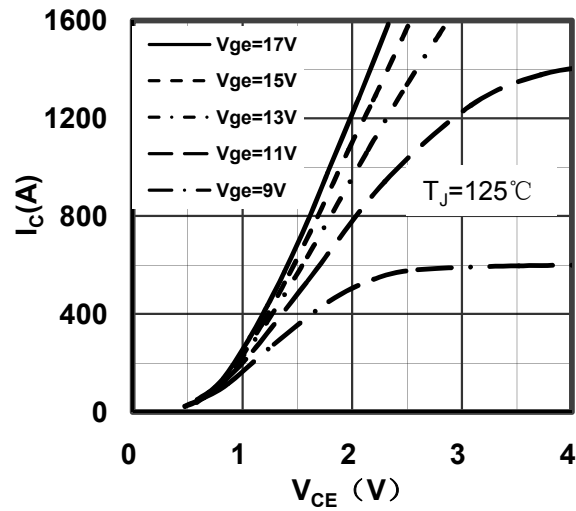


Figure 2. Typical Output Characteristics IGBT-Inverter

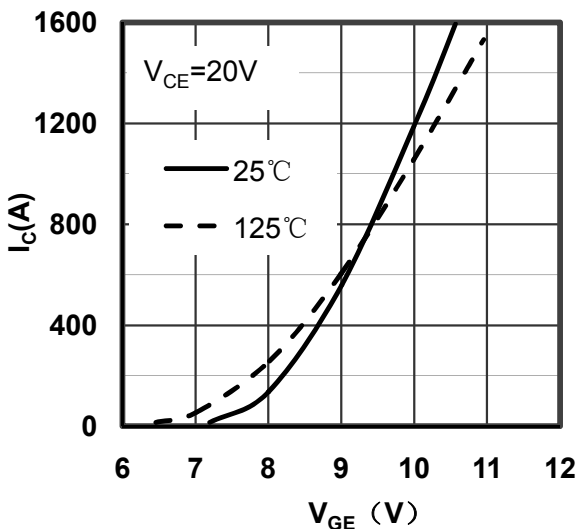


Figure 3. Typical Transfer Characteristics IGBT-Inverter

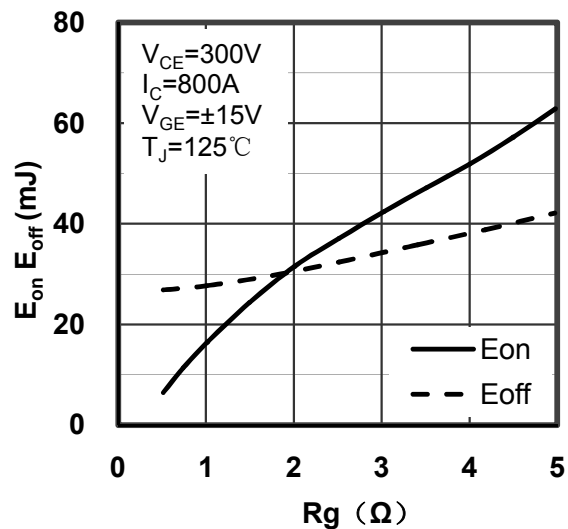


Figure 4. Switching Energy vs Gate Resistor IGBT-Inverter

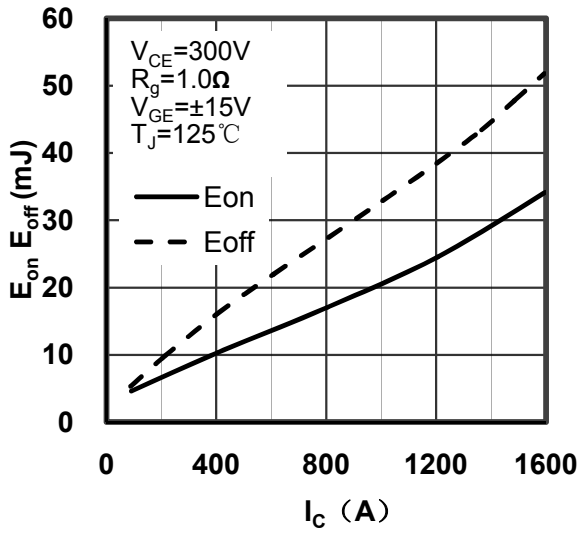


Figure 5. Switching Energy vs Collector Current IGBT-Inverter

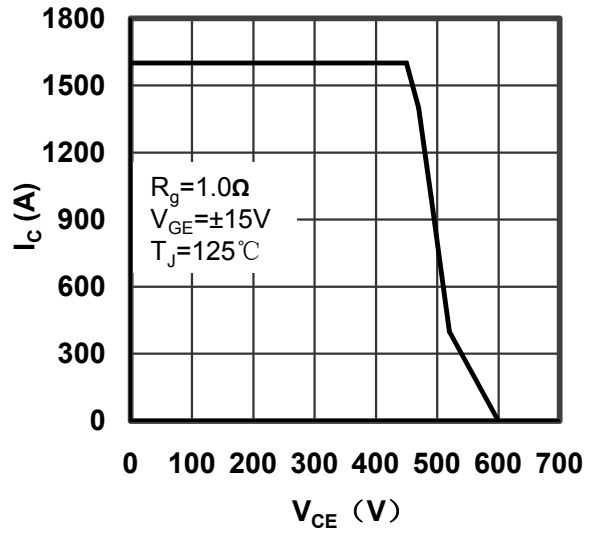


Figure 6. Reverse Biased Safe Operating Area IGBT-Inverter

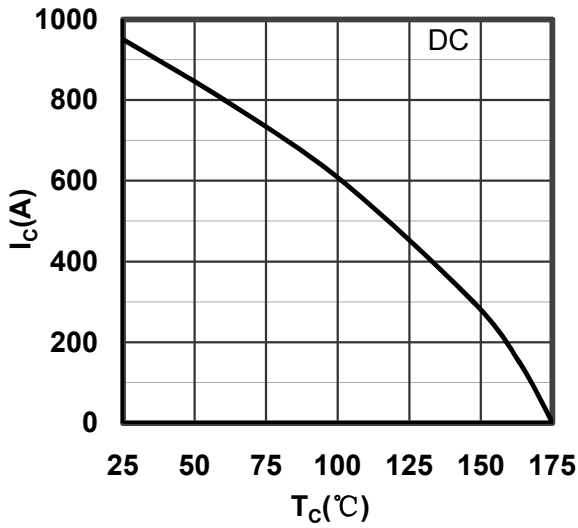


Figure 7. Collector Current vs Case temperature IGBT-Inverter

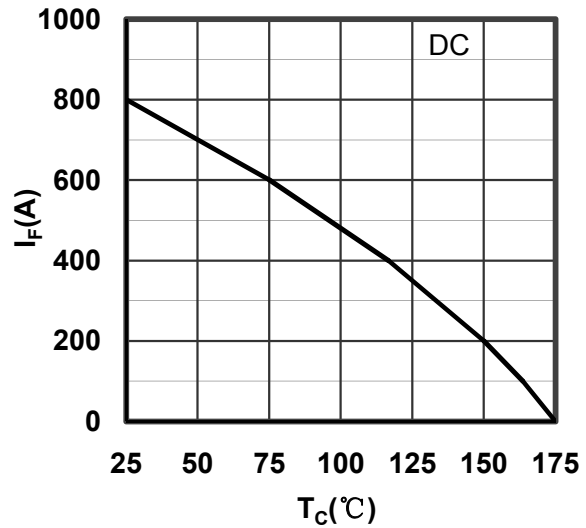


Figure 8. Forward current vs Case temperature Reverse-Diode

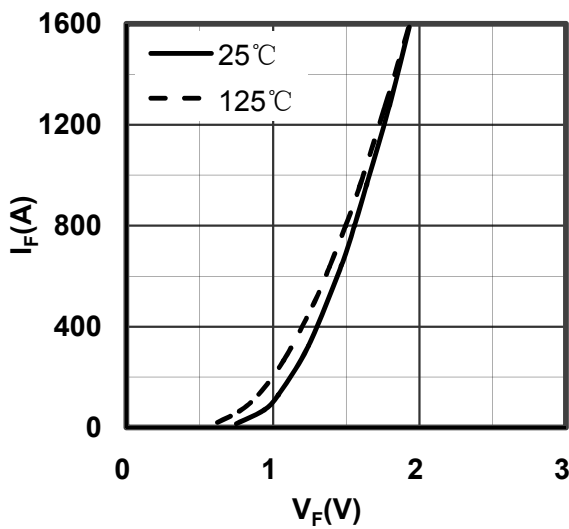


Figure 9. Diode Forward Characteristics Reverse-Diode

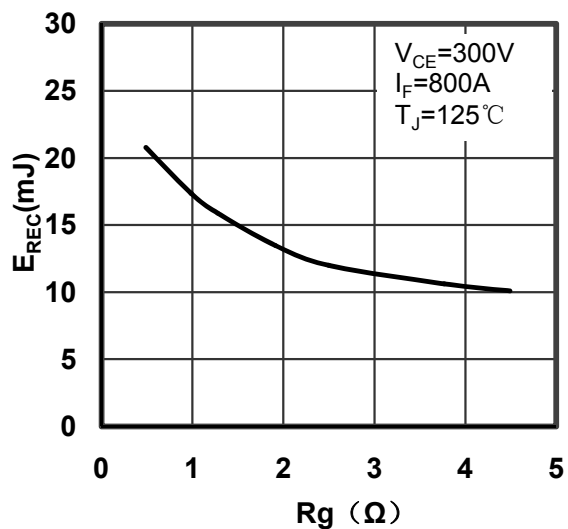


Figure 10. Switching Energy vs Gate Resistor Reverse-Diode

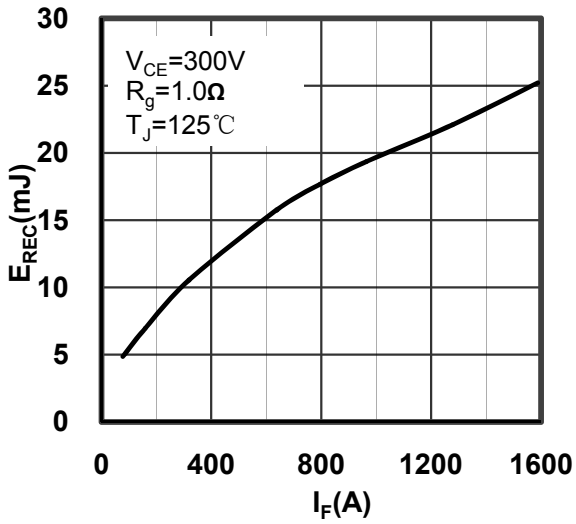


Figure 11. Switching Energy vs Forward Current Reverse-Diode

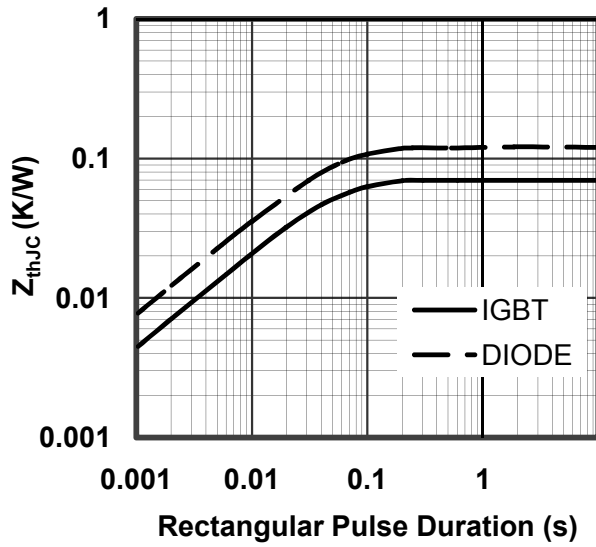
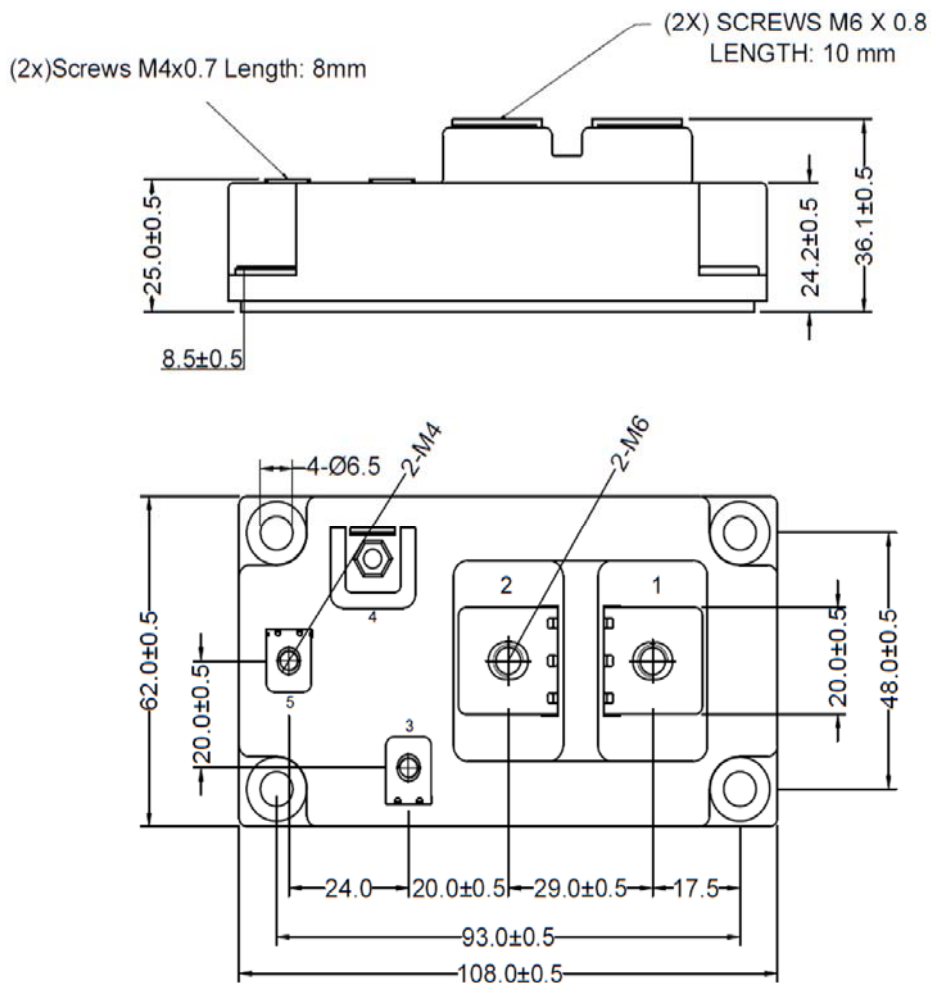


Figure 12. Transient Thermal Impedance of IGBT-Inverter and Reverse-Diode



Dimensions in (mm)
Figure 13. Package Outline